



· Motor drivers, printer hammer drivers, relay drivers, voltage regulator control.

- High DC current gain.
- High current capacity and wide ASO.
- Low saturation voltage.

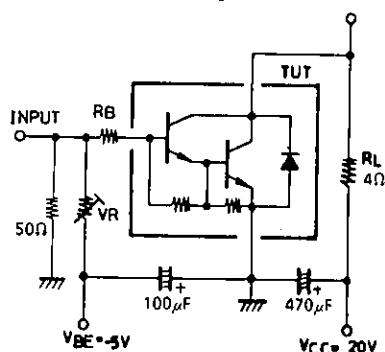
Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

Absolute Maximum Ratings at Ta = 25°C			unit
Collector-to-Base Voltage	V _{CBO}	(-)70	V
Collector-to-Emitter Voltage	V _{CEO}	(-)60	V
Emitter-to-Base Voltage	V _{EBO}	(-)6	V
Collector Current	I _C	(-)10	A
Collector Current (Pulse)	I _{CP}	(-)15	A
Collector Dissipation	P _C	1.75	W
	T _c = 25°C	40	W
Junction Temperature	T _j	150	°C
Storage Temperature	T _{stg}	-55 to +150	°C

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector Cutoff Current	I_{CBO}	$V_{CB}=(-)40V, I_E=0$			$(-)0.1$	mA
Emitter Cutoff Current	I_{EBO}	$V_{EB}=(-)5V, I_C=0$			$(-)3.0$	mA
DC Current Gain	h_{FE}	$V_{CE}=(-)2V, I_C=(-)5A$	2000	5000		
Gain Bandwidth Product	f_T	$V_{CE}=(-)5V, I_C=(-)5A$		20		MHz
C-E Saturation Voltage	$V_{CE(sat)}$	$I_C=(-)5A, I_B=(-)10mA$		0.9	$(-)1.5$	V
				(-1.0)		
B-E Saturation Voltage	$V_{BE(sat)}$	$I_C=(-)5A, I_B=(-)10mA$			$(-)2.0$	V
C-B Breakdown Voltage	$V_{(BR)CBO}$	$I_C=(-)5mA, I_E=0$	$(-)70$			V
C-E Breakdown Voltage	$V_{(BR)CEO}$	$I_C=(-)50mA, R_{BE}=\infty$	$(-)60$			V
Rise Time	t_{on}	See specified Test Circuit.		(0.5)0.6		μs
Storage Time	t_{stg}	"		(1.5)3.0		μs
Fall Time	t_f	"		(1.7)1.8		μs

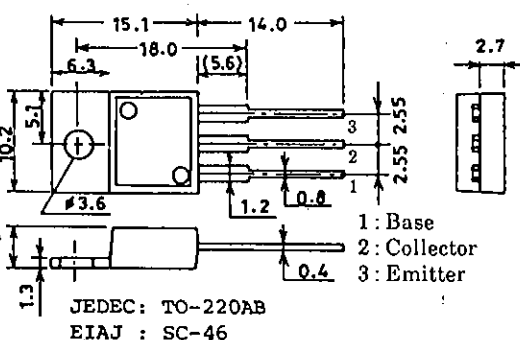
(For PNP, the polarity is reversed.)

$PW = 50 \mu s$, Duty Cycle $\leq 1\%$
 $500I_{B1} = -500I_{B2} = I_C = 5A$

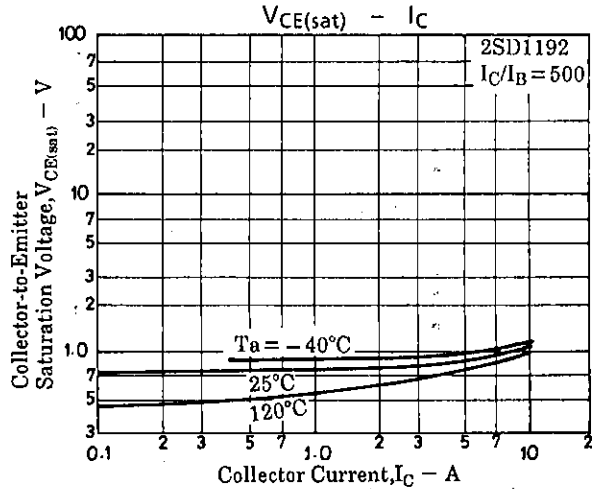
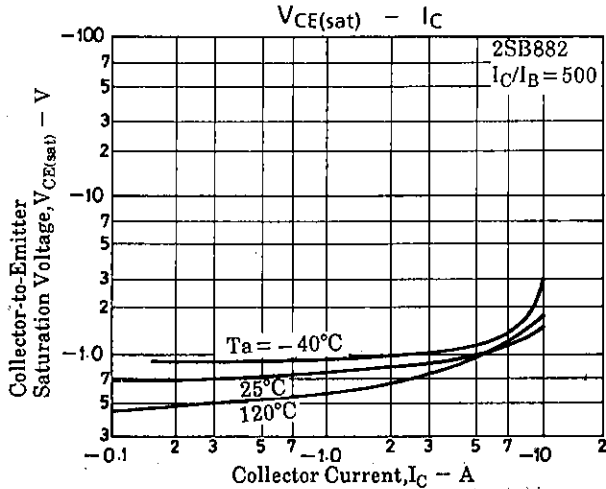
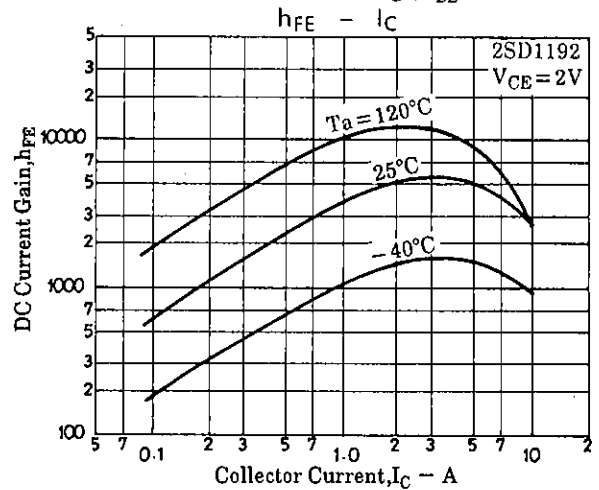
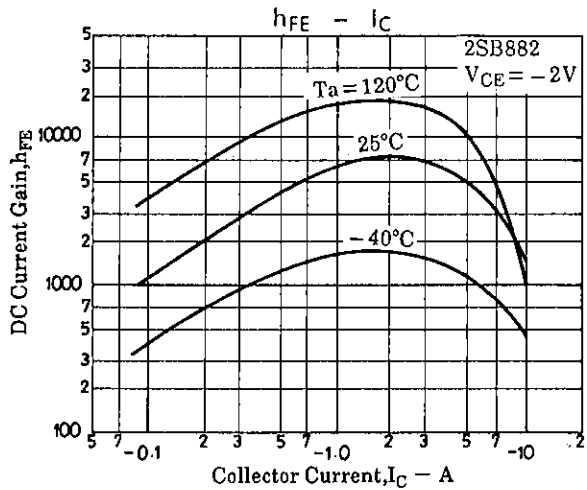
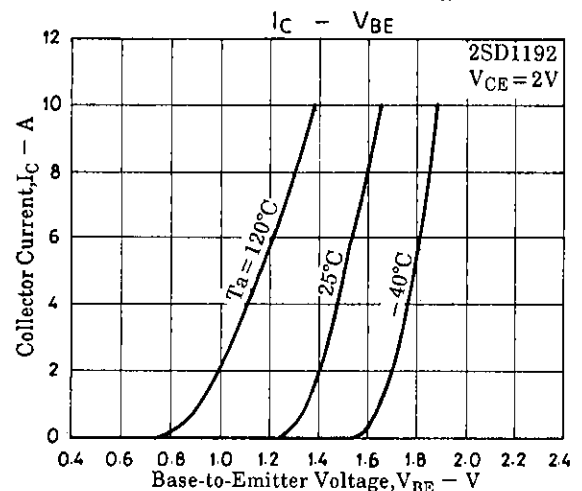
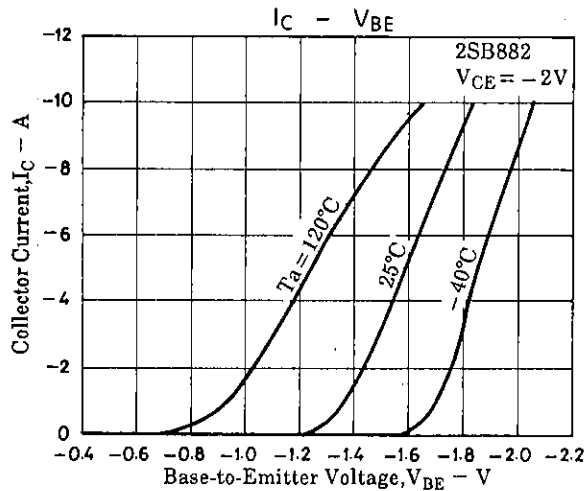
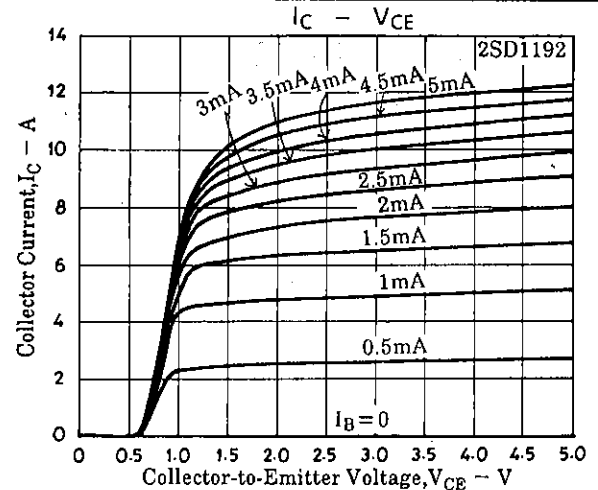
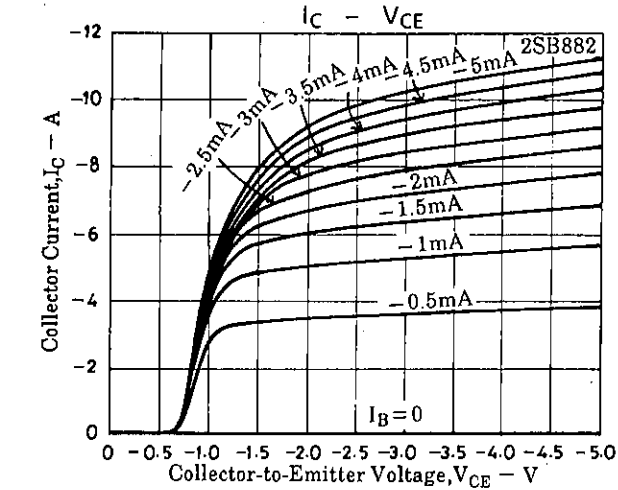


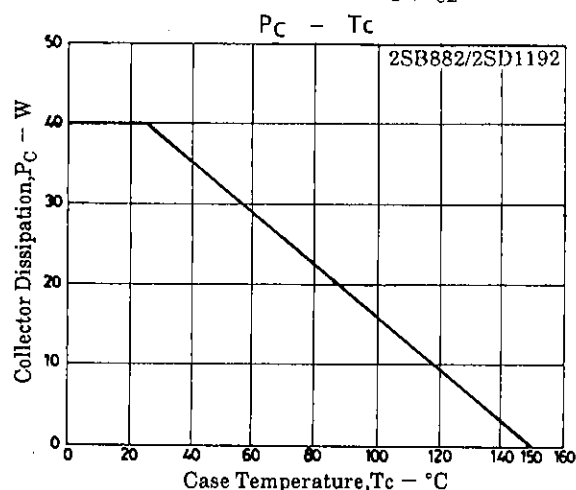
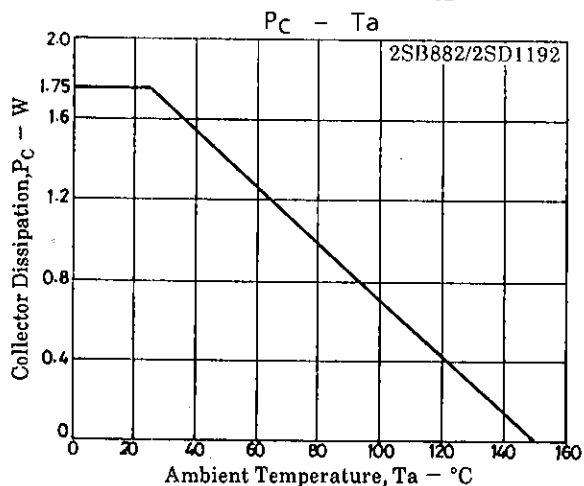
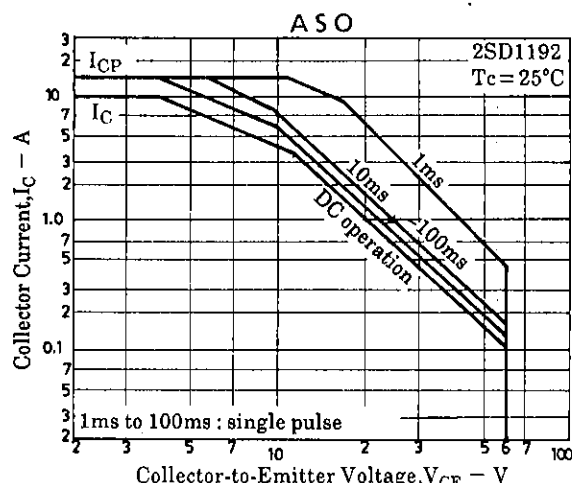
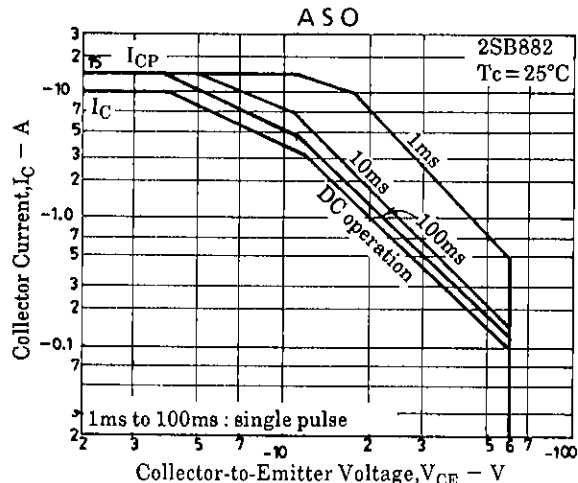
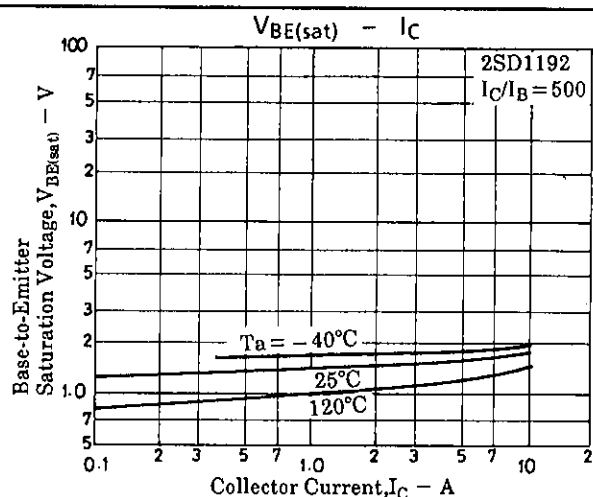
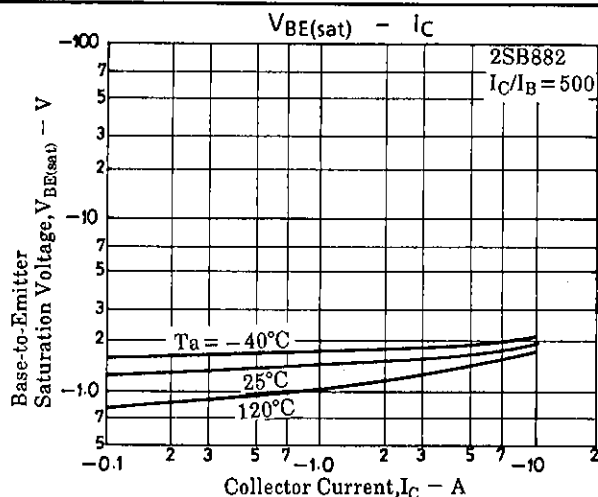
The image shows two circuit diagrams for transistors. The top diagram is for a 2SB882 PNP transistor. It features a common-emitter configuration with a base resistor of 6kΩ and an emitter resistor of 200Ω. The collector is connected to a load (represented by a circle with a dot) and a capacitor C. The emitter is connected to ground (E). A diode is connected in parallel with the emitter resistor. The bottom diagram is for a 2SD1192 NPN transistor. It has a similar common-emitter configuration with a base resistor of 6kΩ and an emitter resistor of 200Ω. The collector is connected to a load and a capacitor C. The emitter is connected to ground (E). A diode is connected in parallel with the emitter resistor.

(unit : mm)



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